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Sheet 1 of 2

Form 1449*	Atty. Docket No.: 303.684US2	Serial No. <u>Unknown</u>
INFORMATION DISCLOSURE STATEMENT BY APPLICANT (Use several sheets if necessary)	Applicant: Leonard Forbes	10/042924
	Filing Date: Herewith 01/09/02	Group: <u>Unknown</u> 2813

PTO
10/042924
11002 US
01/09/02

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Examiner <u>William Alegria</u>	Date Considered <u>7-11-2003</u>
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*Substitute Disclosure Statement Form (PTO-1449)

**EXAMINER: Initial if citation considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

Form 1449*	Atty. Docket No.: 303.684US2	Serial No. Unknown 10/042924
INFORMATION DISCLOSURE STATEMENT BY APPLICANT (Use several sheets if necessary)	Applicant: Leonard Forbes	
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W. H. Lee

Date Considered

7-11-03

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Substitute for form 1449A/PTO INFORMATION DISCLOSURE STATEMENT BY APPLICANT (Use as many sheets as necessary)	Complete if Known	
	Application Number	10/042924
	Filing Date	January 9, 2002
	First Named Inventor	Forbes, Leonard
	Group Art Unit	2822 2813
	Examiner Name	Unknown VESPERMAN
Sheet 1 of 1		Attorney Docket No: 303.684US2

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Examiner Initials*	Cite No ¹	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.		

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